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RSS105N03

Transistor

Switching (30V, ±10.5A)

RSS105N03

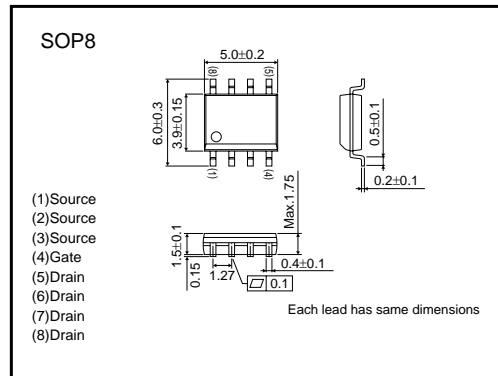
●Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small and Surface Mount Package (SOP8).

●Applications

Power switching, DC/DC converter.

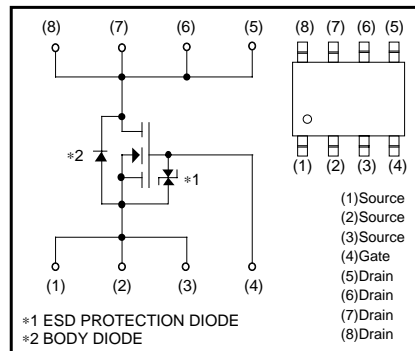
●External dimensions (Unit : mm)



●Structure

- Silicon N-channel MOS FET

●Equivalent circuit



*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V _{DSS}	30	V
Gate-source voltage	V _{GSS}	20	V
Drain current	Continuous	I _D	±10.5 A
	Pulsed	I _{DP}	±42 A *1
Source current (Body diode)	Continuous	I _S	1.6 A
	Pulsed	I _{SP}	6.4 A *1
Total power dissipatino	P _D	2	W *2
Channel temperature	T _{ch}	150	°C
Strage temperature	T _{stg}	-55 to +150	°C

*1 Pw≤10μs, Duty cycles≤1%
 *2 Mounted on a ceramic board.

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●Thermal resistance (Ta=25°C)

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)	62.5	°C / W *

* Mounted on a ceramic board.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	10	μA	V _{GS} =20V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR) DSS}	30	-	-	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	10	μA	V _{DS} =30V, V _{GS} =0V
Gate threshold voltage	V _{GS(th)}	1.0	-	2.5	V	V _{DS} =10V, I _D =1mA
Static drain-source on-starte resistance	R _{DS(on)}	-	8.5	11.7	mΩ	I _D =±10.5A, V _{GS} =10V *
		-	11.4	15.8		I _D =±10.5A, V _{GS} =4.5V *
		-	12.4	17.2		I _D =±10.5A, V _{GS} =4V *
Forward transfer admittance	Y _{fs}	7.0	-	-	S	I _D =±10.5A, V _{DS} =10V *
Input capacitance	C _{iss}	-	1130	-	pF	V _{DS} =10V
Output capacitance	C _{oss}	-	350	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	-	210	-	pF	f=1MHz
Turn-on delay time	t _{d(on)}	-	9	-	ns	I _D =5.25A, V _{DD} =15V *
Rise time	t _r	-	16	-	ns	V _{GS} =10V *
Turn-off delay time	t _{d(off)}	-	53	-	ns	R _L =2.86Ω *
Fall time	t _f	-	22	-	ns	R _{GS} =10Ω *
Total gate charge	Q _g	-	15	-	nC	V _{DD} =15V *
Gate-source charge	Q _{gs}	-	2.9	-	nC	V _{GS} =5V *
Gate-drain charge	Q _{gd}	-	5.9	-	nC	I _D =±10.5A *

*Pulsed

●Body diode characteristics (Source-Drain Characteristics) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _{SD}	-	-	1.2	V	I _S =6.4A, V _{GS} =0V *

*Pulsed

●Electrical characteristic curves

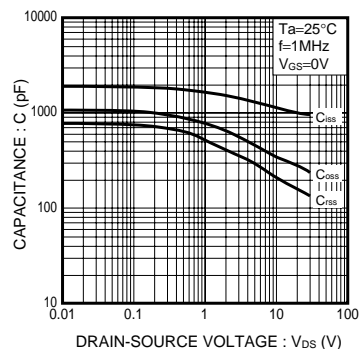


Fig.1 Typical Capacitance vs. Drain-Source Voltage

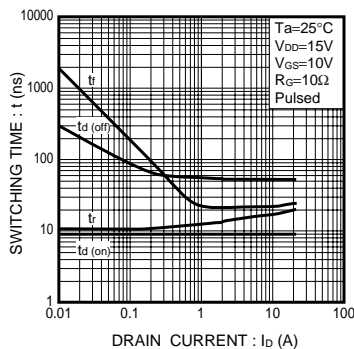


Fig.2 Switching Characteristics

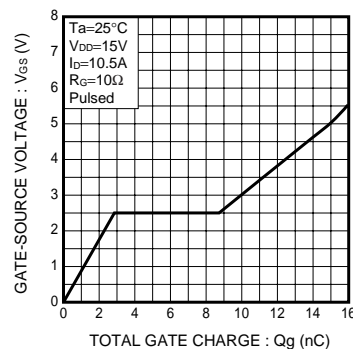


Fig.3 Dynamic Input Characteristics

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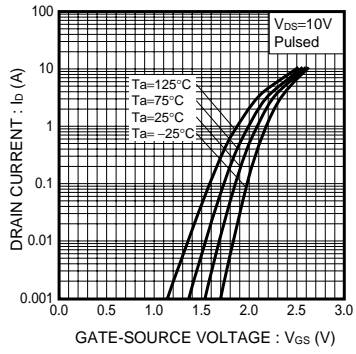


Fig.4 Typical Transfer Characteristics

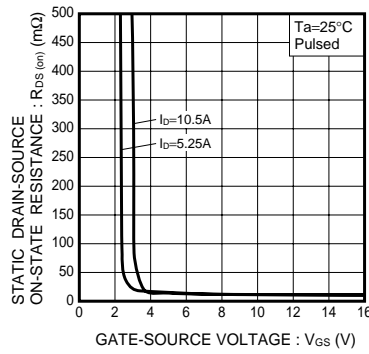


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

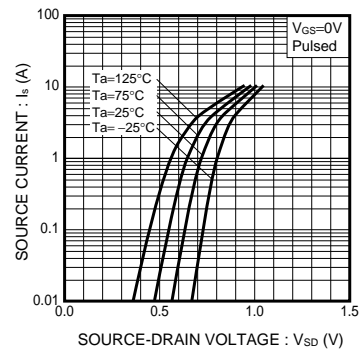


Fig.6 Source Current vs. Source-Drain Voltage

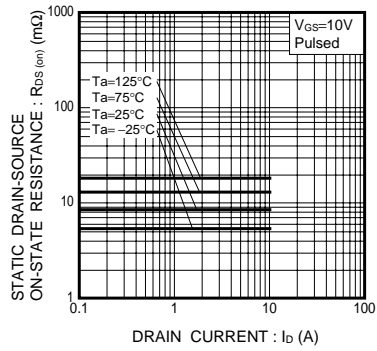


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

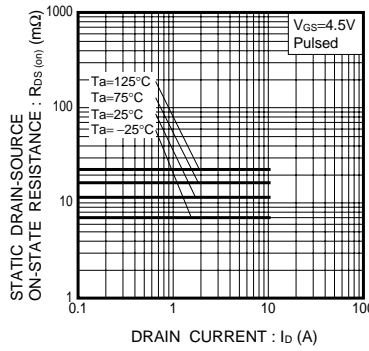


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

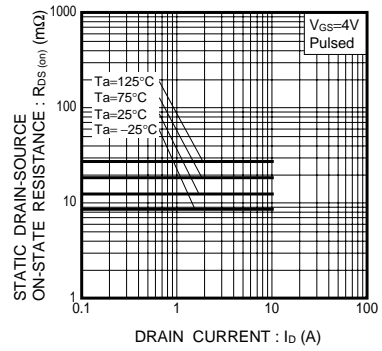


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (III)

Appendix

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